

isc N-Channel MOSFET Transistor

2SK1916

DESCRIPTION

- Drain Current $-I_D=18A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=450V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

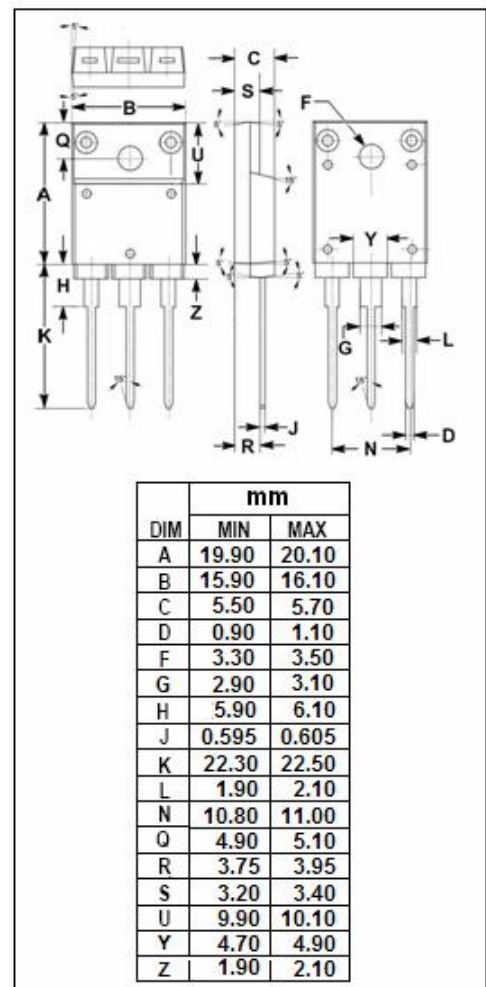
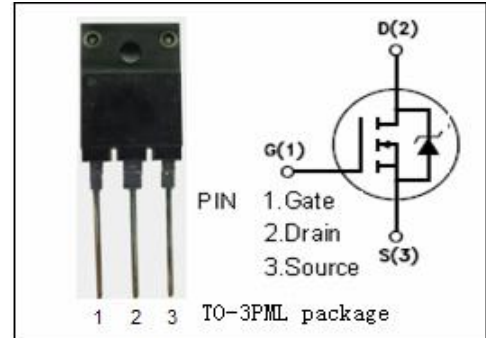
- Switching regulator
- UPS
- General purpose power amplifier

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	450	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	18	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	80	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.56	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	30	$^\circ C/W$



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• ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=1\text{mA}$	450			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=1\text{mA}$	2.5		5	V
V_{DF}	Body to drain diode forward voltage	$I_F=4\text{A}, V_{GS}=0$		0.92	1.41	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=8\text{A}$		0.3	0.45	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 30\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=450\text{V}; V_{GS}=0$			500	μA
C_{iss}	Input capacitance	$V_{DS}=25\text{V}; V_{GS}=0\text{V}; f_T=1\text{MHz}$		1800	2700	pF
C_{rss}	Reverse transfer capacitance			120	185	
C_{oss}	Output capacitance			270	410	
t_r	Rise time	$V_{GS}=10\text{V}; I_D=18\text{A};$ $V_{DD}=300\text{V};$ $R_L=25\Omega$		100	150	ns
t_{on}	Turn-on time			70	110	
t_f	Fall time			80	120	
t_{off}	Turn-off time			250	380	